

RADIANT TECHNOLOGIES PATENT LIST.

| Patent #. | Title : |
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| 1) 6.505.137 | Method for operating a test system. |
| 2) 6.459.137 | Method for constructing ferroelectric capacitors on integrated circuit substrates. |
| 3) 6.417.110 | Method for constructing heat resistant electrode structures on silicone substrates. |
| 4) 6.225.654 | Static ferroelectric memory transistor having improved data retention. |
| 5) 6.194.751 | Ferroelectric based memory devices utilizing low Curie point ferroelectrics and encapsulation. |
| 6) 6.121.648 | Ferroelectric based memory devices utilizing hydrogen getters and recovery annealing. |
| 7) 6.117.688 | Method for constructing ferroelectric based capacitors for use in memory systems. |
| 8) 6.074.885 | Lead titanate isolation layers for use in fabricating PZT-based capacitors and similar structures. |
| 9) 6.066.868 | Ferroelectric based memory devices utilizing hydrogen barriers and getters. |
| 10) 5.977.577 | Ferroelectric based memory devices utilizing low Curie point ferroelectrics and encapsulation |
| 11) 5.963.466 | Ferroelectric memory having a common plate electrode. |
| 12) 5.892.255 | Ferroelectric based capacitor for use in memory systems and method for fabricating the same. |
| 13) 5.872.739 | Sense amplifier for low read-voltage memory cells. |
| 14) 5.804.850 | Ferroelectric based capacitor cell for use in memory systems. |
| 15) 5.757.042 | High density ferroelectric memory with increased channel modulation and double word ferroelectric memory cell for constructing the same. |
| 16) 5.679.969 | Ferroelectric based capacitor for use in memory systems and method for fabricating the same. |
| 17) 5.614.438 | Method for making LSCO stack electrode. |
| 18) 5.593.914 | Method for constructing ferroelectric capacitor-like structures on Silicone Dioxide. |
| 19) 5.453.347 | Method for constructing ferroelectric capacitors on integrated circuit substrates. |
| 20) 5.440.173 | High-temperature electrical contact for making contact to ceramic materials and improved circuit element using the same. |
| 21) 5.240.428 | Infra-Red sensing array. |
| 22) 5.242.534 | Platinum lift-off process. |
| 23) 5.239.399 | Electrical-optical interface device. |
| 24) 5.232.747 | Platinum –Aluminum connection system. |
| 25) 5.212.620 | Method for isolating SiO.sub.2 layers from PZT.PLZT and Platinum layers. |
| 26) 5.179.533 | Read/Write optical memory. |
| 27) 5.164.808 | Platinum electrode structure for use in conjunction with ferroelectric materials. |
| 28) 5.119.329 | Memory cell based on ferroelectric non- volatile variable resistive element. |
| 29) 5.109.156 | Light actuated optical logic device. |
| 30) 5.078.478 | Light actuated optical switching device. |
| 31) 5.070.385 | Ferroelectric non-volatile variable resistive element. |
| 32) 5.051.950 | Read/Write optical memory. |